



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

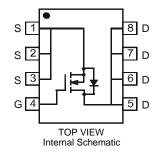
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)

SO-8



TOP VIEW



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25^{\circ}C$ $T_A = 85^{\circ}C$	ID	10 6	A
Pulsed Drain Current (Note 4)			I _{DM}	60	A
Avalanche Current (Notes 4 & 5)			I _{AR}	8	A
Repetitive Avalanche Energy (Notes 4 & 5) L = 0.1mH		E _{AR}	3.2	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	PD	1.42	W
Thermal Resistance, Junction to Ambient @TA = 25°C (Note 3)	R _{θJA}	88.49	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Notes: 1.

No purposefully added lead.
Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. Device mounted on 1 in.² FR-4 board with 2oz. Copper, in a still air environment @ T_A = 25°C. The value in any given application depends on the user's specific board design.

4. Repetitive rating, pulse width limited by junction temperature.

5. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = 25^{\circ}C$

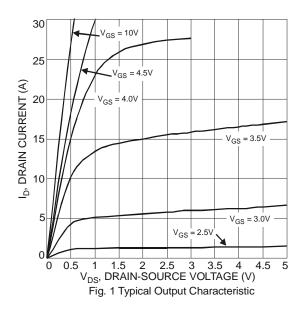


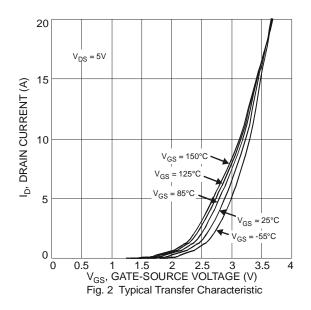
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.8	1.2	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		-	16	21.5	mΩ	$V_{GS} = 10V, I_D = 10A$	
	R _{DS (ON)}		22	29		$V_{GS} = 4.5 V, I_D = 7.5 A$	
Forward Transfer Admittance	Y _{fs}	-	11.7	-	S	$V_{DS} = 5V, I_{D} = 10A$	
Diode Forward Voltage	V _{SD}	-	0.70	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	-	493.5	-	pF		
Output Capacitance	C _{oss}	-	94.5	-	PF $V_{DS} = 15V, V_{GS} = 0V$	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	50.4	-	pF	-f = 1.0 MHz	
Gate Resistance	R _g	-	2.86	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	4.7	-	nC	$V_{DS} = 15V, V_{GS} = 4.5V, ID = 10/$	
Total Gate Charge (V _{GS} = 10V)	Qg	-	10.2	-	nc		
Gate-Source Charge	Q _{gs}	-	1.4	-	nC	V _{DS} = 15V, V _{GS} = 10V, ID =10A	
Gate-Drain Charge	Q _{gd}	-	1.7	-	nC		
Turn-On Delay Time	t _{D(on)}	-	4.76	-	ns		
Turn-On Rise Time	tr	-	3.64	-	ns	V _{GS} = 10V, V _{Ds} = 15V,	
Turn-Off Delay Time	t _{D(off)}	-	19.5	-	ns	$R_{G} = 6\Omega, R_{L} = 15\Omega,$	
Turn-Off Fall Time	t _f	-	4.9	-	ns		

ctrical Charactoristics

Notes:

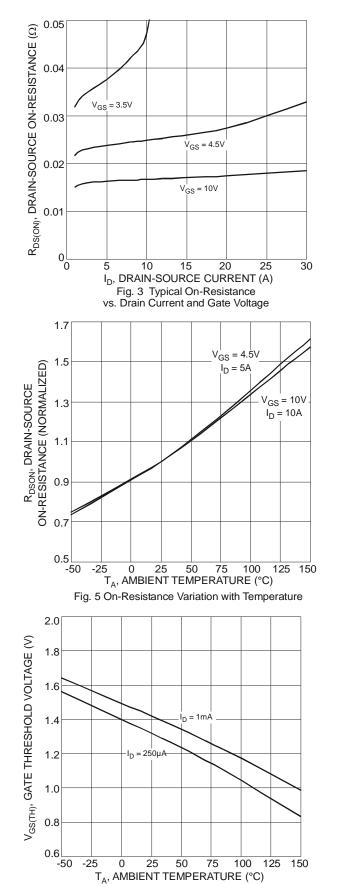
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.



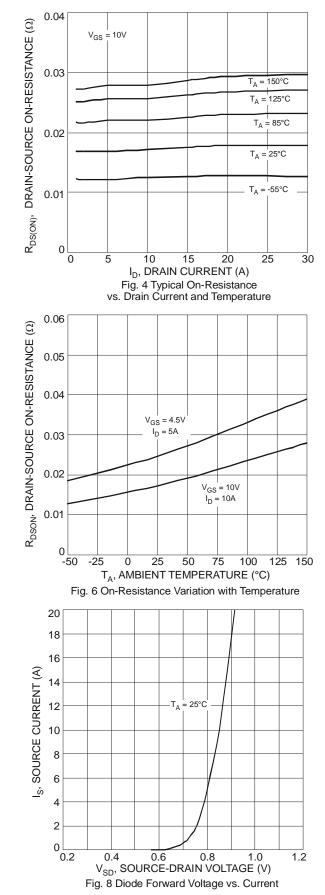




NEW PRODUCT

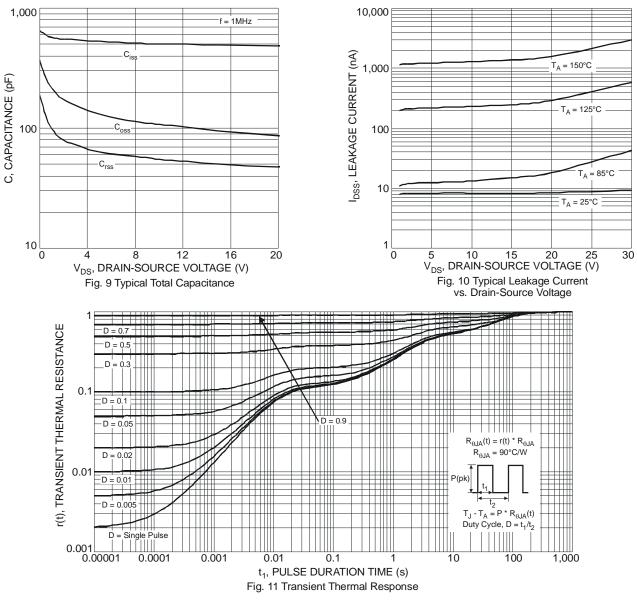








DMG4496SSS

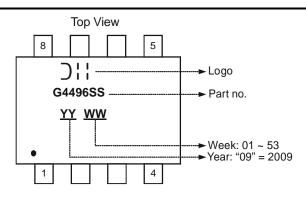


Ordering Information (Note 8)

Part Number	Case	Packaging		
DMG4496SSS-13	SO-8	2500 / Tape & Reel		

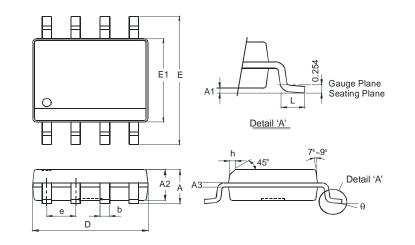
Notes: 8. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



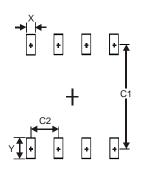


Package Outline Dimensions



SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
ш	5.90	6.10		
E1	3.85	3.95		
e	1.27 Тур			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Di	All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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